

PRELIMINARY AMENDMENT
U.S. Appln. No. 09/987,049

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width of approximately 50 μ m. A p-side electrode 118 is formed on said stripe region. An n-side electrode is formed on the reverse surface of the substrate 100. Note that the oscillation wavelength band of this semiconductor laser is 440nm, and the width of its emission range is 50 μ m. Therefore, the output obtainable therefrom is on the order of 2W, and its light conversion rate is approximately 15%. Laser light emitted from twenty five of these semiconductor lasers is input into a fiber with a core diameter of 500 μ m to obtain a fiber excitation module 122 having an output of 50W.

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Page 30, last paragraph bridging page 31, delete and insert the following:

As shown in Figure 16, at the fiber 140, the laser beam 133 is amplified by receiving energy from fluorescent materials of the same wavelength (1560nm), and is emitted from the emission terminal surface 140b of said fiber 140. The laser beam 133, having a wavelength of 1560nm, is focused by the focusing lens 154 and enters the wavelength conversion portion 156. The laser beam 133 is converted into a fourth harmonic thereof at the wavelength conversion portion, and is emitted therefrom as a laser beam 137 having a wavelength of 390nm. Note that an output of 5W can be obtained by this fiber laser.